

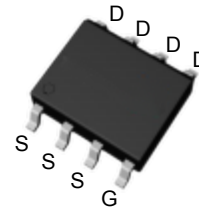
Features

- -40V/-6A ,
 $R_{DS(ON)} = 33m\Omega (typ.) @ V_{GS} = -10V$
 $R_{DS(ON)} = 44m\Omega (typ.) @ V_{GS} = -4.5V$
- 100% UIS + R_g Tested
- Reliable and Rugged
- Lead Free and Green Devices Available (RoHS Compliant)

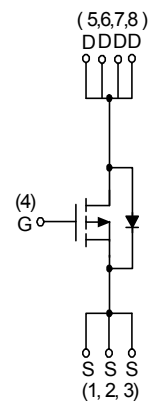
Applications

- DC/DC Converter.
- Power Management.
- Load Switch.
- For Motor Drive Application.

Pin Description



Top View of SOP-8



P-Channel MOSFET

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter		Rating	Unit
Common Ratings				
V _{DSS}	Drain-Source Voltage		-40	V
V _{GSS}	Gate-Source Voltage		±20	
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-55 to 150	
I _S	Diode Continuous Forward Current	T _A =25°C	-6	A
I _D	Continuous Drain Current	T _A =25°C	-6	A
		T _A =70°C	-2.4	
I _{DM} ^a	Pulsed Drain Current	T _C =25°C	-24	
P _D	Maximum Power Dissipation	T _A =25°C	1.56	W
		T _A =70°C	1	
R _{θJA} ^b	Thermal Resistance-Junction to Ambient		80	°C/W
I _{AS} ^c	Avalanche Current, Single pulse	L=0.5mH	-17	A
E _{AS} ^c	Avalanche Energy, Single pulse	L=0.5mH	72	mJ

Note a : Pulse width limited by max. junction temperature.

Note b : Surface Mounted on 1in^2 pad area.

Note c : UIS tested and pulse width limited by maximum junction temperature 150°C (initial temperature $T_J=25^\circ\text{C}$).

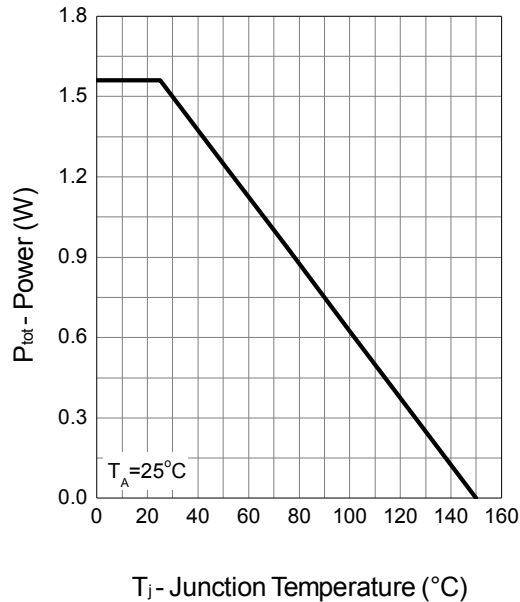
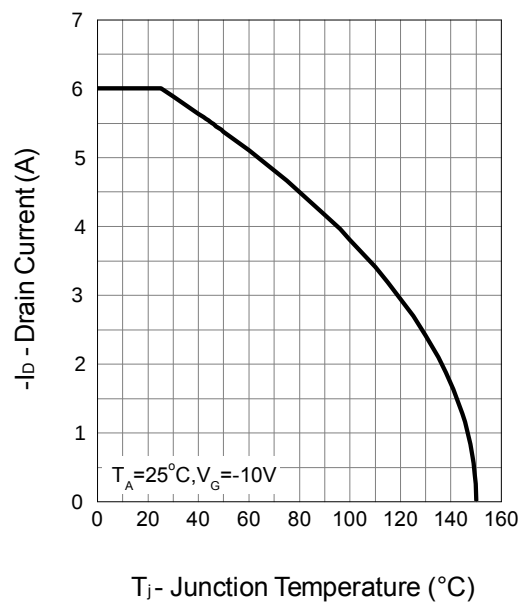
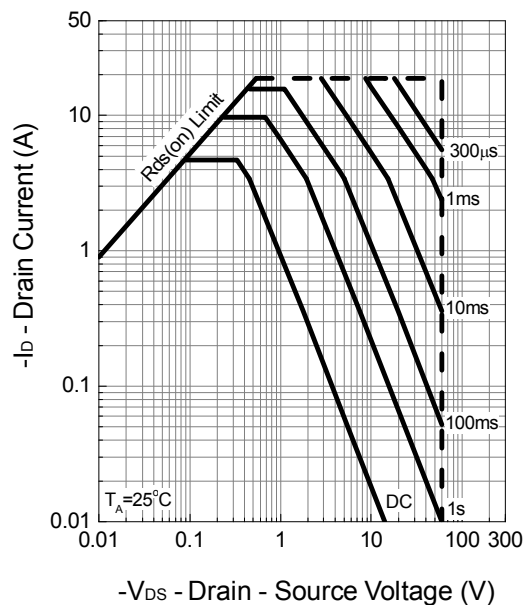
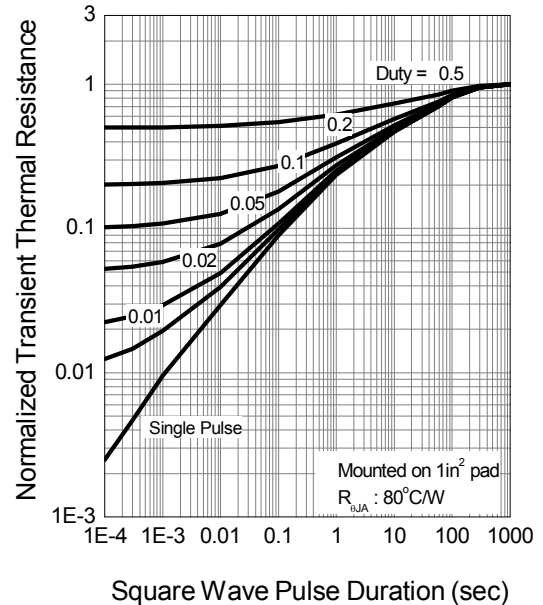
Electrical Characteristics (T_A = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =-250μA	-40	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-32V, V _{GS} =0V T _J =85°C	-	-	-1 -30	μA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =-250μA	-1.0	-1.5	-2.5	V
I _{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
R _{DS(ON)} ^d	Drain-Source On-state Resistance	V _{GS} =-10V, I _{DS} =-4A V _{GS} =-4.5V, I _{DS} =-3A	- -	33 44	46 65	mΩ mΩ
Diode Characteristics						
V _{SD} ^d	Diode Forward Voltage	I _{SD} =-1A, V _{GS} =0V	-	-0.7	-1.1	V
t _{rr}	Reverse Recovery Time	I _{SD} =-4A, dI _{SD} /dt=100A/μs	-	26	-	ns
Q _{rr}	Reverse Recovery Charge		-	33	-	nC
Dynamic Characteristics ^e						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz	-	8	16	Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =-30V, Frequency=1.0MHz	-	1416	1840	pF
C _{oss}	Output Capacitance		-	142	-	
C _{rss}	Reverse Transfer Capacitance		-	85	-	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =-30V, R _L =30Ω, I _{DS} =-1A, V _{GEN} =10V, R _G =6Ω	-	10	18	ns
t _r	Turn-on Rise Time		-	9	16	
t _{d(OFF)}	Turn-off Delay Time		-	88	158	
t _f	Turn-off Fall Time		-	42	76	
Gate Charge Characteristics ^e						
Q _g	Total Gate Charge	V _{DS} =-30V, V _{GS} =-4.5V, I _{DS} =-4A	-	15.6	-	nC
Q _g	Total Gate Charge	V _{DS} =-30V, V _{GS} =-10V, I _{DS} =-4A	-	32	45	
Q _{gs}	Gate-Source Charge		-	5.2	-	
Q _{gd}	Gate-Drain Charge		-	6.8	-	

Note d : Pulse test; pulse width≤300μs, duty cycle≤2%.

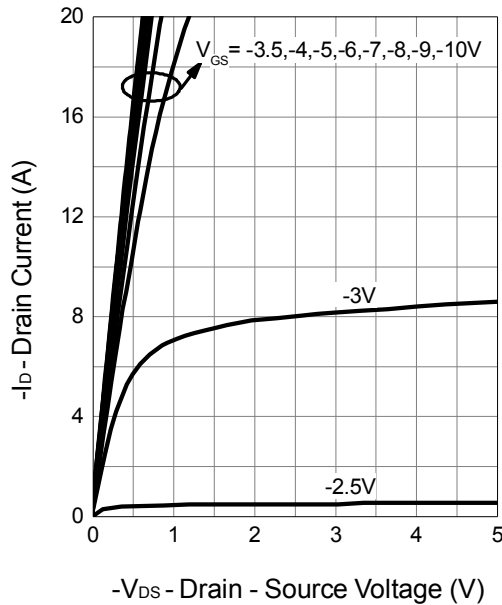
Note e : Guaranteed by design, not subject to production testing.

Typical Characteristics

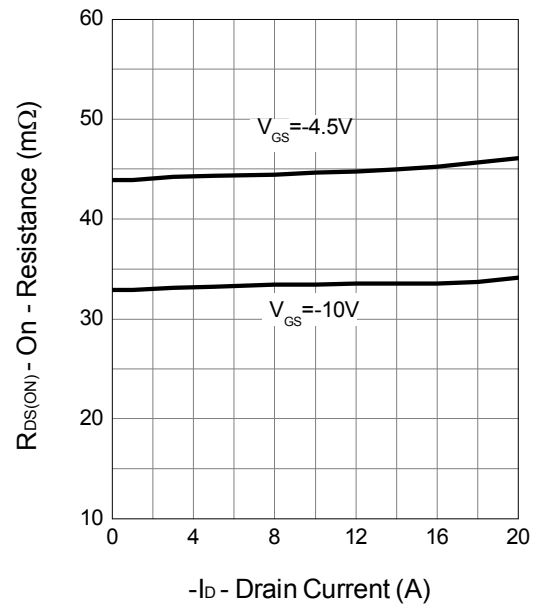
Power Dissipation

Drain Current

Safe Operation Area

Thermal Transient Impedance


Typical Characteristics (Cont.)

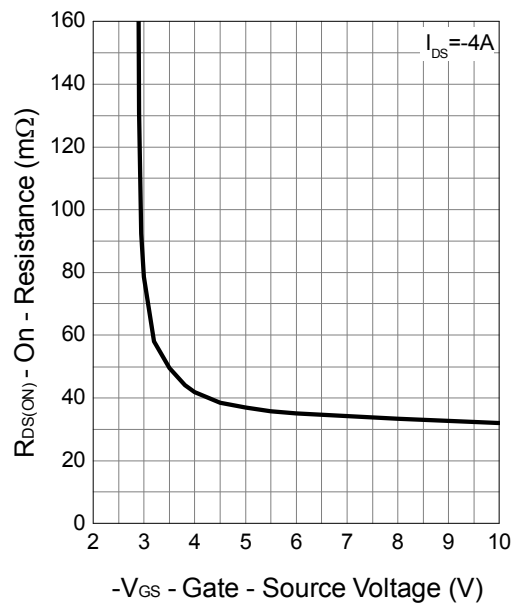
Output Characteristics



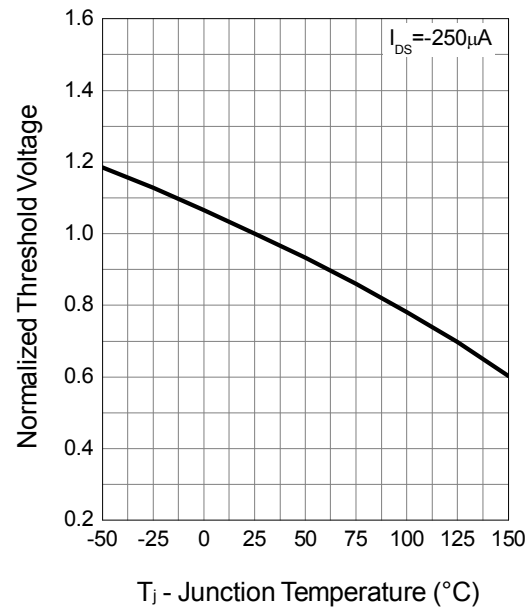
Drain-Source On Resistance



Gate-Source On Resistance

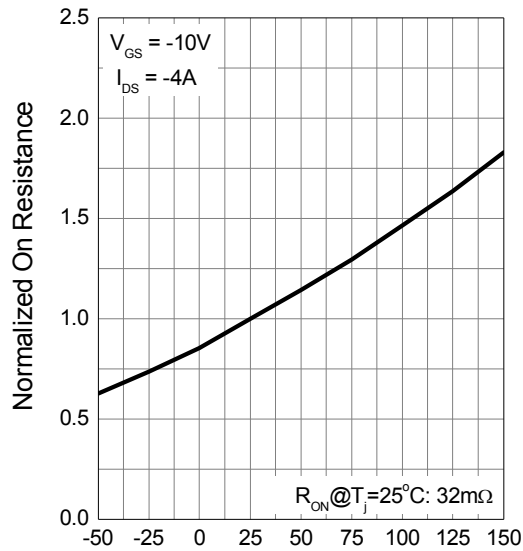


Gate Threshold Voltage



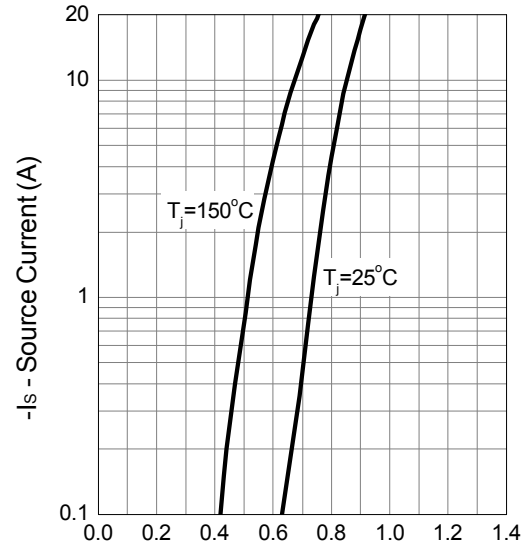
Typical Characteristics (Cont.)

Drain-Source On Resistance



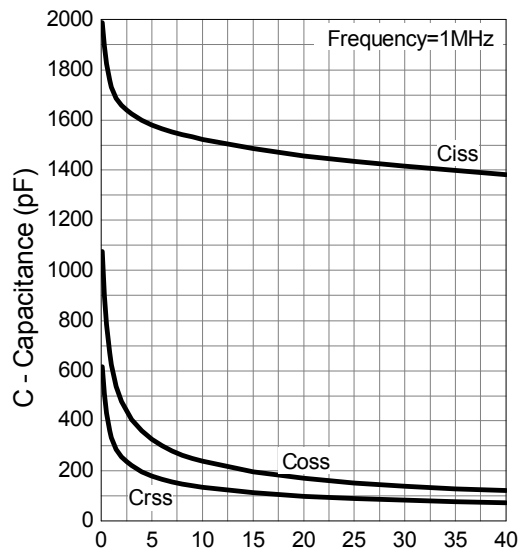
T_j - Junction Temperature ($^{\circ}\text{C}$)

Source-Drain Diode Forward



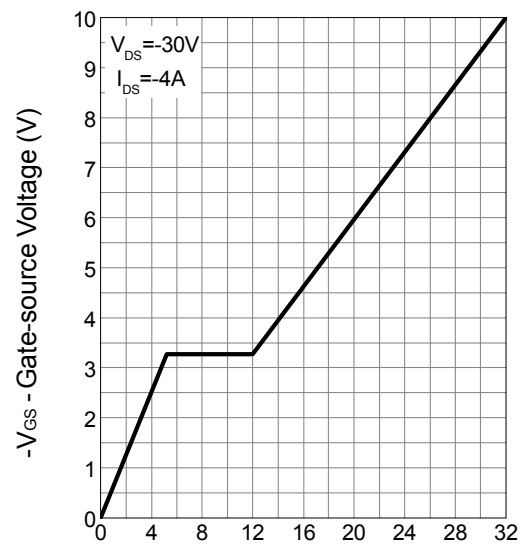
$-V_{SD}$ - Source - Drain Voltage (V)

Capacitance



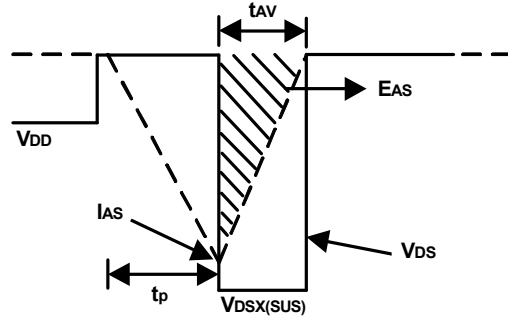
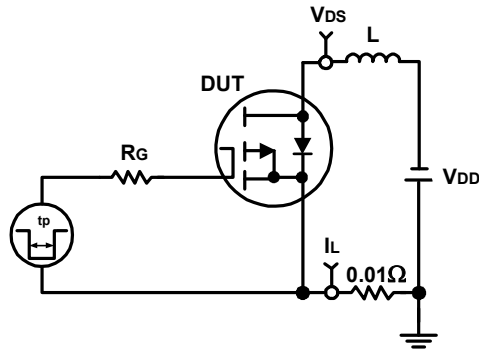
$-V_{DS}$ - Drain - Source Voltage (V)

Gate Charge

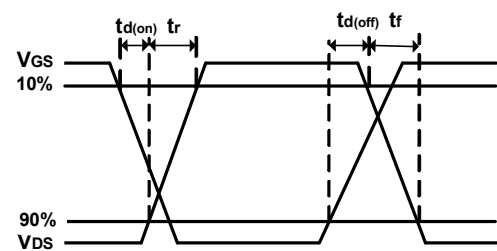
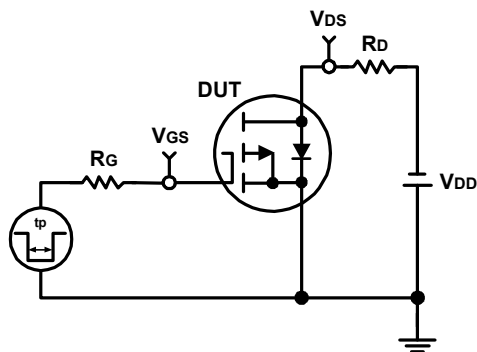


Q_G - Gate Charge (nC)

Avalanche Test Circuit and Waveforms

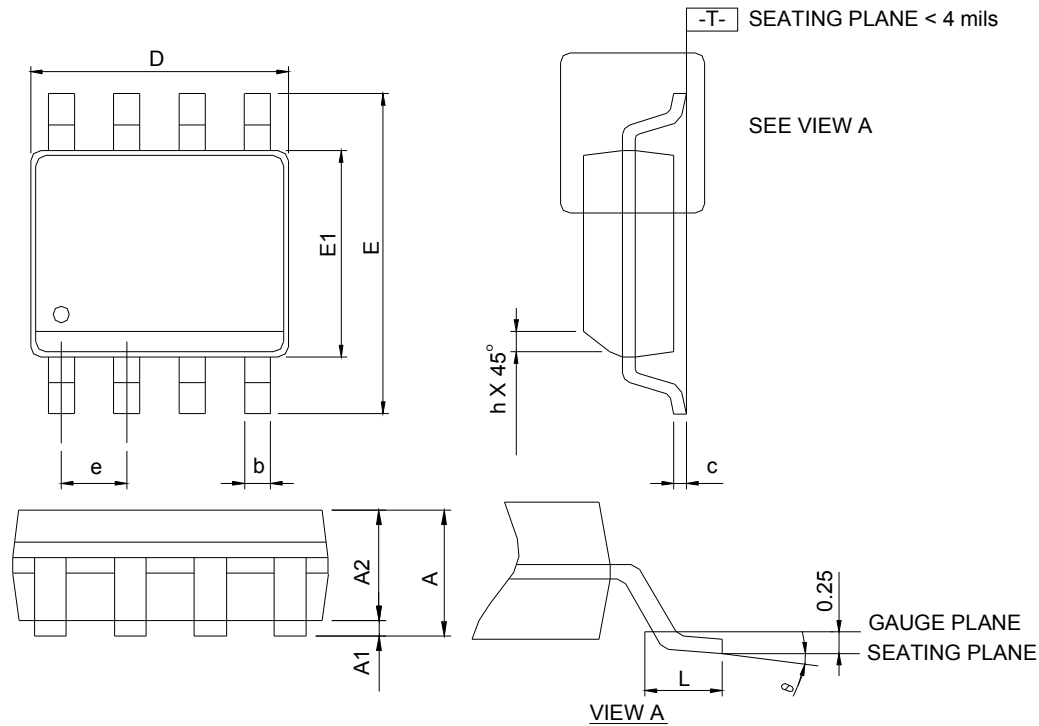


Switching Time Test Circuit and Waveforms



Package Information

SOP-8



SOP-8	SOP-8			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	-	1.75	-	0.069
A1	0.10	0.25	0.004	0.010
A2	1.25	-	0.049	-
b	0.31	0.51	0.012	0.020
c	0.17	0.25	0.007	0.010
D	4.80	5.00	0.189	0.197
E	5.80	6.20	0.228	0.244
E1	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
h	0.25	0.50	0.010	0.020
L	0.40	1.27	0.016	0.050
θ	0°	8°	0°	8°

Note: 1. Follow JEDEC MS-012 AA.

2. Dimension "D" does not include mold flash, protrusions or gate burrs. Mold flash, protrusion or gate burrs shall not exceed 6 mil per side.

3. Dimension "E" does not include inter-lead flash or protrusions. Inter-lead flash and protrusions shall not exceed 10 mil per side.

RECOMMENDED LAND PATTERN

